Erratum: Realization of a heavily doped and fully compensated semiconductor state in a crystalline semiconductor with a deep impurity band [JETP 84, 309–316 (February 1997)]

M. I. Daunov, I. K. Kamilov, and A. B. Magomedov

Institute of Physics, Dagestan Science Center, Russian Academy of Sciencees, 367003 Makhachkala, Russia [S1063-7761(97)02406-2]

The following corrections were reported by the authors. On page 309 in the right-hand column, in the 10th line from the bottom, the equation should read as follows: $N_d^+ = N_{d\mu}^+ + N_{dr}^+$. On the same page and the same column, in the 9th line from the bottom, the equation should read as follows: $N_a = N_{ar}^- + N_{a\mu}^- + N_A$. Also on the same page and the same column, in the 2nd line from the bottom, the equation should read as follows: $N = N_d^+ - (N_{a\mu}^- + N_{ar}^-)$.

In the first part of Table II, in the 11th column, in the second line from the bottom, the number should read as follows: 0.02.